

**Amendments to the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method for manufacturing an electro-optical substrate including a composite base plate obtained by joining a support plate to a semiconductor plate having semiconductor layers, comprising:

forming a light-shielding layer, having a predetermined pattern, ~~on~~over a support plate;

forming an insulating layer ~~on~~over the light-shielding layer having the predetermined pattern;

providing a semiconductor layerslayer over ~~on~~ the insulating layer;

partially oxidizing ~~parts of the semiconductor layerslayer~~ to form an oxide layerslayer; and

removing the oxide ~~layerslayer~~, the oxide ~~layerslayer~~ having a thickness smaller than that of the insulating layer.

2. (Currently Amended) The method for manufacturing an electro-optical substrate according to Claim 1, further comprising:

patterning the semiconductor ~~layerslayer~~; and

oxidizing parts of the semiconductor ~~layerslayer~~ having a predetermined pattern to form the oxide ~~layerslayer~~,

the patterning step and oxidizing step being performed after the semiconductor layer-providing step.

3. (Currently Amended) The method for manufacturing an electro-optical substrate according to Claim 1, further comprising:

oxidizing parts of the semiconductor ~~layerslayer~~ to form gate oxide layers,

the semiconductor layer-oxidizing step being performed after the oxide layer-removing step.

4. (Currently Amended) The method for manufacturing an electro-optical substrate according to Claim 1, the oxide ~~layerslayer~~ having a thickness smaller than that of parts of the insulating layer disposed in areas above which the semiconductor ~~layers are~~layer is not placed, and which are disposed on the light-shielding layer.

5. (Original) The method for manufacturing an electro-optical substrate according to Claim 1, further comprising:

forming a silicon nitride layer or silicon oxide nitride layer between the light-shielding layer and the insulating layer.

6. (Currently Amended) The method for manufacturing an electro-optical substrate according to Claim 1, the semiconductor layer-providing step including a sub-step of joining a single-crystal semiconductor plate including the semiconductor ~~layers~~layer to a support plate including the insulating layer.

7. (Original) The method for manufacturing an electro-optical substrate according to Claim 1, the light-shielding layer containing a high-melting metal or a silicide containing a high-melting metal.

8. (Original) A method for manufacturing an electro-optical apparatus including a semiconductor element, comprising manufacturing an electro-optical substrate including the semiconductor element by the manufacturing method according to Claim 1.

9. Cancelled.